

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended): A method for removing structures to be removed, which comprises the steps of:

providing a substrate, ~~forming~~ having the structures to be removed on the substrate, the structures to be removed having with an aspect ratio of greater than 2 and being formed from a material selected from the group consisting of noble metals, oxides of noble metals, and ferroelectric materials;

depositing a sacrificial layer on the structures to be removed and the substrate; and

removing the structures to be removed and the sacrificial layer in a polishing step.

Claims 2-3 (cancelled)

Claim 4 (original): The method according to claim 1, which comprises carrying out a chemical mechanical polishing process as the polishing step.

Claim 5 (previously presented): The method according to claim 1, which comprises forming the sacrificial layer from at least one of a silicon oxide layer and a silicon nitride layer.

Claim 6 (previously presented): The method according to claim 4, which comprises removing residues of the sacrificial layer by wet chemical processes following the chemical mechanical polishing process.

Claim 7 (original): The method according to claim 1, which comprises forming the structures that must be removed with an aspect ratio of greater than 4.

Claim 8 (previously presented): A method for producing at least one structured layer, which comprises the steps of:

providing a substrate;

applying at least one layer to the substrate for structuring;

applying a mask to the layer to be structured;

etching the layer being structured by a dry etching method, so that redepositions of the layer emerge at sidewalls of the mask;

removing the mask;

applying a sacrificial layer; and

performing a polishing step to remove the redepositions of the layer being structured, and to remove the sacrificial layer, so that a structured layer emerges.

Claim 9 (original): The method according to claim 8, which comprises forming the layer from a material selected from the group consisting of noble metals, an oxide of the noble metals, a dielectric material and a ferroelectric material.

Claim 10 (original): The method according to claim 8, which comprises interrupting the polishing step and removing residues of the mask.

Claim 11 (original): The method according to claim 8, which comprises performing a chemical mechanical polishing process as the polishing step.

Claim 12 (previously presented): The method according to claim 8, which comprises forming the sacrificial layer from at least one of a silicon oxide layer and a silicon nitride layer.